





80V NPN DARLINGTON TRANSISTOR IN SOT223

Features

- BV_{CEO} > 80V
- BV_{CBO} > 100V
- I_C = 2A High Continuous Current
- Useful hFE up to 6A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

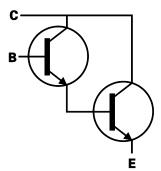
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.112 grams (Approximate)

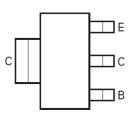




Top View



Device Symbol



Top View Pin-Out

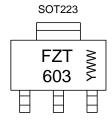
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT603TA	FZT603	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information



FZT 603 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	10	V
Continuous Collector Current	Ic	2	Α
Peak Pulse Current	Ісм	6	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 5)		3.0		
Power Dissipation	(Note 6)	D-	2.0	W	
Power Dissipation	(Note 7)	P _D	1.6		
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	D	62.5		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ hetaJL}$	12.9		
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Notes:

- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

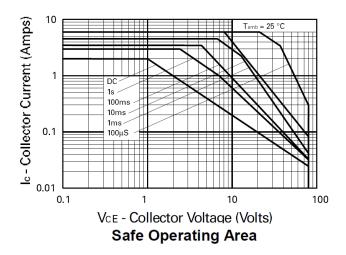
 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.

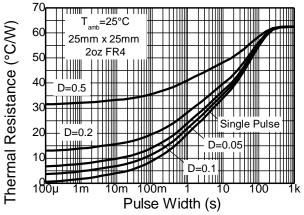
 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.

- 8. Same as Note 5, except the device is mounted on minimum recommended pad layout.
 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





50

T = 25°C

40

50mm x 50mm
20z FR4

20

D=0.5

D=0.2

10

D=0.2

Single Pulse

D=0.05

D=0.1

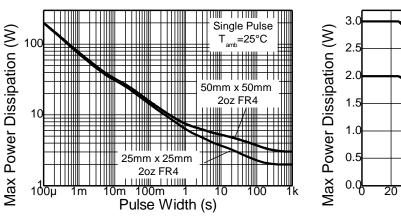
D=0.05

Pulse Width (s)

Transient Thermal Impedance

Transient Thermal Impedance

Pulse Power Dissipation



3.0 2.5 50mm x 50mm 20z FR4 25mm x 25mm 20z FR4 1.5 1.0 0.0 20 40 60 80 100 120 140 160 Temperature (°C)

Derating Curve



FZT603

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

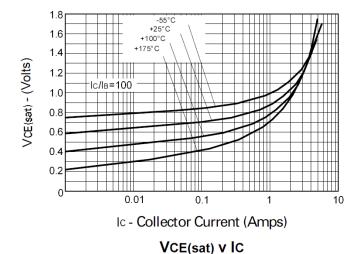
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	100	240	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	80	110	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	10	16	_	V	I _E = 100μA
Collector-Base Cut-Off Current	I _{CBO}	- -	_	10 10	nΑ μΑ	V _{CB} = 80V V _{CB} = 80V, T _A = +100°C
Collector-Emitter Cut-Off Current	I _{CES}	-	_	10	μA	V _{CES} = 80V
Emitter Cutoff Current	I _{EBO}	-	_	100	nA	V _{EB} = 8V
DC Current Gain (Note 11)	h _{FE}	3,000 5,000 3,000 2,000	14,000 15,000 14,000 10,000 2,000 750	100,000 — — — —	_	$\begin{split} & I_{C} = 50 \text{mA}, V_{CE} = 5 \text{V} \\ & I_{C} = 500 \text{mA}, V_{CE} = 5 \text{V} \\ & I_{C} = 1 \text{A}, V_{CE} = 5 \text{V} \\ & I_{C} = 2 \text{A}, V_{CE} = 5 \text{V} \\ & I_{C} = 5 \text{A}, V_{CE} = 5 \text{V} \\ & I_{C} = 6 \text{A}, V_{CE} = 5 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}		0.79 0.80 0.88 0.99 0.86	0.88 0.90 1.00 1.13	V	$I_C = 250\text{mA}, I_B = 0.25\text{mA}$ $I_C = 0.4\text{A}, I_B = 0.4\text{mA}$ $I_C = 1\text{A}, I_B = 1\text{mA}$ $I_C = 2\text{A}, I_B = 20\text{mA}$ $I_C = 2\text{A}, I_B = 20\text{mA}, T_J = +150^{\circ}\text{C}$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	1.70	1.95	V	$I_C = 2A$, $I_B = 20mA$
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	1.50	1.75	V	$I_C = 2A, V_{CE} = 5V$
Input Capacitance (Note 11)	C _{ibo}	_	90	_	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance (Note 11)	C _{obo}	_	15	_	pF	V _{CB} = 10V, f = 1MHz
Current Gain-Bandwidth Product (Note 11)	f⊤	150	_	_	MHz	V _{CE} = 10V, I _C = 100mA, f=20MHz
Turn-On Time	t _{on}	_	0.5	_	μs	V _{CC} = 10V, I _C = 500mA
Turn-Off Time	t _{off}	_	1.6		μs	$I_{B1} = -I_{B2} = 0.5 \text{mA}$

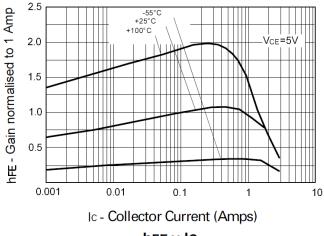
Note:

11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



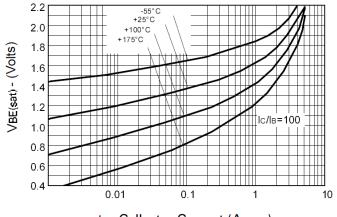
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

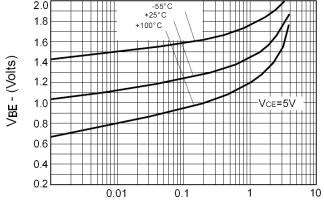




hfe v IC

2.0





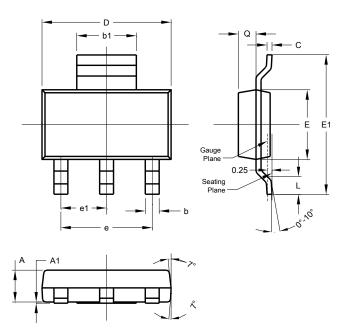
Ic - Collector Current (Amps)

VBE(on) v IC



Package Outline Dimensions

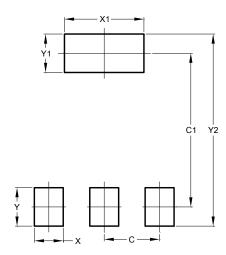
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00





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